# Low Power, Standard Frequency Oscillator



#### **Features**

- 52 standard frequencies between 3.57 MHz and 77.76 MHz
- 100% pin-to-pin drop-in replacement to quartz-based XO
- Excellent total frequency stability as low as ±20 ppm
- Operating temperature from -40°C to 85°C. For 125°C and/or -55°C options, refer to SiT1618, SiT8918, SiT8920
- Low power consumption of 3.5 mA typical at 1.8V
- Standby mode for longer battery life
- Fast startup time of 5 ms
- LVCMOS/HCMOS compatible output
- Industry-standard packages: 2.0 x 1.6, 2.5 x 2.0, 3.2 x 2.5, 5.0 x 3.2, 7.0 x 5.0 mm x mm
- Instant samples with Time Machine II and field programmable oscillators
- RoHS and REACH compliant, Pb-free, Halogen-free and Antimony-free
- For AEC-Q100 oscillators, refer to SiT8924 and SiT8925

#### **Applications**

- Ideal for DSC, DVC, DVR, IP CAM, Tablets, e-Books, SSD, GPON, EPON, etc
- Ideal for high-speed serial protocols such as: USB, SATA, SAS, Firewire, 100M / 1G / 10G Ethernet, etc.







## **Electrical Specifications**

#### **Table 1. Electrical Characteristics**

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage.

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition			
			F	requency R	ange				
Output Frequency Range	f		rd frequencie IHz and 77.7		MHz	Refer to Table 13 for the exact list of supported frequencies			
			Frequer	ncy Stability	and Aging				
Frequency Stability	F_stab	-20	-	+20	ppm	Inclusive of initial tolerance at 25°C, 1st year aging at 25°C, and			
		-25	_	+25	ppm	variations over operating temperature, rated power supply voltage and load.			
		-50	-	+50	ppm	1			
Operating Temperature Range									
Operating Temperature Range	T_use	-20	-	+70	°C	Extended Commercial			
		-40	-	+85	°C	Industrial			
		Sı	ipply Voltag	e and Curre		•			
Supply Voltage	Vdd	1.62	1.8	1.98	V	Contact SiTime for 1.5V support			
		2.25	2.5	2.75	V				
		2.52	2.8	3.08	V				
		2.7	3.0	3.3	V				
		2.97	3.3	3.63	V				
		2.25	-	3.63	V				
Current Consumption	ldd	_	3.8	4.5	mA	No load condition, f = 20 MHz, Vdd = 2.8V to 3.3V			
		_	3.7	4.2	mA	No load condition, f = 20 MHz, Vdd = 2.5V			
		-	3.5	4.1	mA	No load condition, f = 20 MHz, Vdd = 1.8V			
OE Disable Current	I_OD	_	_	4.2	mA	Vdd = 2.5V to 3.3V, OE = GND, Output in high-Z state			
		-	-	4.0	mA	Vdd = 1.8 V. OE = GND, Output in high-Z state			
Standby Current	I_std	-	2.6	4.3	μΑ	ST = GND, Vdd = 2.8V to 3.3V, Output is weakly pulled down			
		-	1.4	2.5	μΑ	ST = GND, Vdd = 2.5V, Output is weakly pulled down			
		_	0.6	1.3	μА	ST = GND, Vdd = 1.8V, Output is weakly pulled down			
	•		LVCMOS	Output Cha	aracteristic	s			
Duty Cycle	DC	45	_	55	%	All Vdds. See Duty Cycle definition in Figure 3 and Footnote 6			
Rise/Fall Time	Tr, Tf	_	1	2	ns	Vdd = 2.5V, 2.8V, 3.0V or 3.3V, 20% - 80%			
		_	1.3	2.5	ns	Vdd =1.8V, 20% - 80%			
		_	_	2	ns	Vdd = 2.25V - 3.63V, 20% - 80%			
Output High Voltage	VOH	90%	-	-	Vdd	IOH = -4 mA (Vdd = 3.0V or 3.3V) IOH = -3 mA (Vdd = 2.8V and Vdd = 2.5V) IOH = -2 mA (Vdd = 1.8V)			
Output Low Voltage	VOL	-	-	10%	Vdd	IOL = 4 mA (Vdd = 3.0V or 3.3V) IOL = 3 mA (Vdd = 2.8V and Vdd = 2.5V) IOL = 2 mA (Vdd = 1.8V)			

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**Table 1. Electrical Characteristics (continued)** 

		-	-			
Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition
			Inp	ut Charact	eristics	
Input High Voltage	VIH	70%	_	_	Vdd	Pin 1, OE or ST
Input Low Voltage	VIL	-	-	30%	Vdd	Pin 1, OE or ST
Input Pull-up Impedance	Z_in	50	87	150	kΩ	Pin 1, OE logic high or logic low, or ST logic high
		2	-	-	MΩ	Pin 1, ST logic low
			Startu	p and Resu	me Timing	·
Startup Time	T_start	_	_	5	ms	Measured from the time Vdd reaches its rated minimum value
Enable/Disable Time	T_oe	-	-	138	ns	f = 77.76 MHz. For other frequencies, T_oe = 100 ns + 3 * cycles
Resume Time	T_resume	-	-	5	ms	Measured from the time ST pin crosses 50% threshold
				Jitter		
RMS Period Jitter	T_jitt	_	1.8	3	ps	f = 75 MHz, Vdd = 2.5V, 2.8V, 3.0V or 3.3V
		-	1.8	3	ps	f = 75 MHz, Vdd = 1.8V
Peak-to-peak Period Jitter	T_pk	-	12	25	ps	f = 75 MHz, Vdd = 2.5V, 2.8V, 3.0V or 3.3V
		=	14	30	ps	f = 75 MHz, Vdd = 1.8V
RMS Phase Jitter (random)	T_phj	_	0.5	0.9	ps	f = 75 MHz, Integration bandwidth = 900 kHz to 7.5 MHz

## **Table 2. Pin Description**

Pin	Symbol	Functionality					
		Output Enable	H <sup>[1]</sup> : specified frequency output L: output is high impedance. Only output driver is disabled.				
1	OE/ ST/NC Standby  No Connect		H <sup>[1]</sup> : specified frequency output L: output is low (weak pull down). Device goes to sleep mode. Supp current reduces to I_std.				
			Any voltage between 0 and Vdd or Open <sup>[1]</sup> : Specified frequency output. Pin 1 has no function.				
2	GND	Power	Electrical ground				
3	OUT	Output	Oscillator output				
4	VDD	Power	Power supply voltage <sup>[2]</sup>				

1.3

# Top View OE/ST/NC 1 4 VDD GND 2 3 OUT

f = 75 MHz, Integration bandwidth = 12 kHz to 20 MHz

Figure 1. Pin Assignments

#### Notes:

- 1. In OE or  $\overline{ST}$  mode, a pull-up resistor of 10 k $\Omega$  or less is recommended if pin 1 is not externally driven. If pin 1 needs to be left floating, use the NC option.
- 2. A capacitor of value 0.1  $\mu\text{F}$  or higher between Vdd and GND is required.

# Low Power, Standard Frequency Oscillator



#### **Table 3. Absolute Maximum Limits**

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
Vdd	-0.5	4	V
Electrostatic Discharge	-	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	-	260	°C
Junction Temperature <sup>[3]</sup>	-	150	°C

#### Note:

## Table 4. Thermal Consideration<sup>[4]</sup>

Package	θJA, 4 Layer Board (°C/W)	θJA, 2 Layer Board (°C/W)	θJC, Bottom (°C/W)
7050	142	273	30
5032	97	199	24
3225	109	212	27
2520	117	222	26
2016	152	252	36

#### Note:

# Table 5. Maximum Operating Junction Temperature<sup>[5]</sup>

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
70°C	80°C
85°C	95°C

#### Note

#### **Table 6. Environmental Compliance**

Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method 2002
Mechanical Vibration	MIL-STD-883F, Method 2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method 2003
Moisture Sensitivity Level	MSL1 @ 260°C

<sup>3.</sup> Exceeding this temperature for extended period of time may damage the device.

<sup>4.</sup> Refer to JESD51 for  $\theta$ JA and  $\theta$ JC definitions, and reference layout used to determine the  $\theta$ JA and  $\theta$ JC values in the above table.

<sup>5.</sup> Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.



#### Test Circuit and Waveform<sup>[6]</sup>

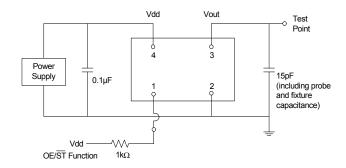


Figure 2. Test Circuit

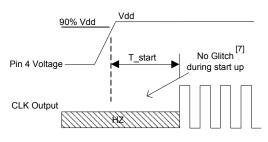
#### Note:

6. Duty Cycle is computed as Duty Cycle = TH/Period.

# tr — tf 80% Vdd 50% 20% Vdd High Pulse (TH) Period Period

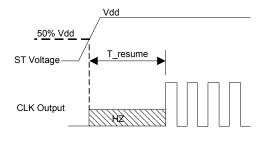
Figure 3. Waveform

## **Timing Diagrams**



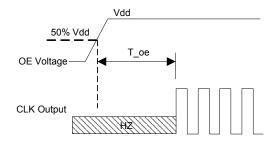
T\_start: Time to start from power-off

Figure 4. Startup Timing (OE/ST Mode)



T\_resume: Time to resume from ST

Figure 5. Standby Resume Timing (ST Mode Only)

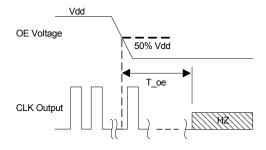


T\_oe: Time to re-enable the clock output

Figure 6. OE Enable Timing (OE Mode Only)

#### Note

7. SiT1602 has "no runt" pulses and "no glitch" output during startup or resume.



T\_oe: Time to put the output in High Z mode

Figure 7. OE Disable Timing (OE Mode Only)



# Performance Plots<sup>[8]</sup>

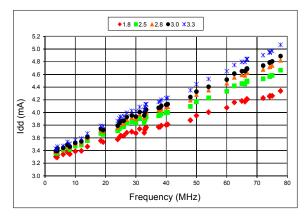


Figure 8. Idd vs Frequency

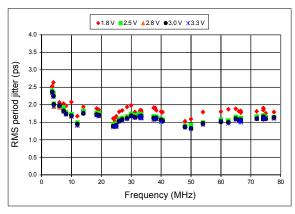


Figure 10. RMS Period Jitter vs Frequency

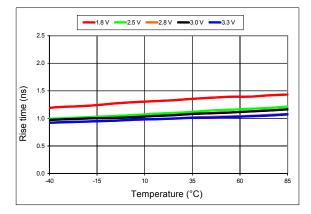


Figure 12. 20%-80% Rise Time vs Temperature

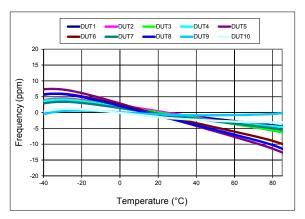


Figure 9. Frequency vs Temperature

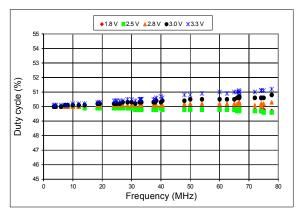


Figure 11. Duty Cycle vs Frequency

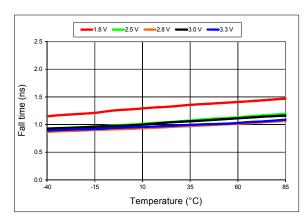


Figure 13. 20%-80% Fall Time vs Temperature

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# Performance Plots<sup>[8]</sup>

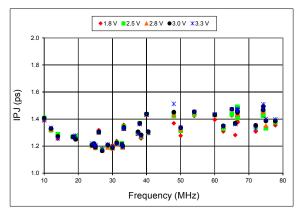


Figure 14. RMS Integrated Phase Jitter Random (12 kHz to 20 MHz) vs Frequency<sup>[9]</sup>

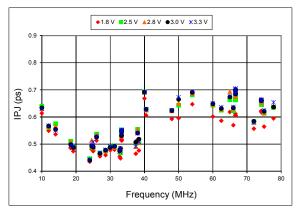


Figure 15. RMS Integrated Phase Jitter Random (900 kHz to 20 MHz) vs Frequency<sup>[9]</sup>

#### Notes:

- 8. All plots are measured with 15 pF load at room temperature, unless otherwise stated.
- 9. Phase noise plots are measured with Agilent E5052B signal source analyzer. Integration range is up to 5 MHz for carrier frequencies below 40 MHz.

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#### **Programmable Drive Strength**

The SiT1602 includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining full swing with sharp edge rates.

For more detailed information about rise/fall time control and drive strength selection, see the SiTime Application Notes section: http://www.sitime.com/support/application-notes.

#### **EMI Reduction by Slowing Rise/Fall Time**

Figure 16 shows the harmonic power reduction as the rise/fall times are increased (slowed down). The rise/fall times are expressed as a ratio of the clock period. For the ratio of 0.05, the signal is very close to a square wave. For the ratio of 0.45, the rise/fall times are very close to near-triangular waveform. These results, for example, show that the 11th clock harmonic can be reduced by 35 dB if the rise/fall edge is increased from 5% of the period to 45% of the period.

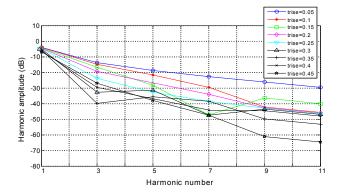


Figure 16. Harmonic EMI reduction as a Function of Slower Rise/Fall Time

#### Jitter Reduction with Faster Rise/Fall Time

Power supply noise can be a source of jitter for the downstream chipset. One way to reduce this jitter is to speed up the rise/fall time of the input clock. Some chipsets may also require faster rise/fall time in order to reduce their sensitivity to this type of jitter. Refer to the Rise/Fall Time Tables (Table 7 to Table 11) to determine the proper drive strength.

#### **High Output Load Capability**

The rise/fall time of the input clock varies as a function of the actual capacitive load the clock drives. At any given drive strength, the rise/fall time becomes slower as the output load increases. As an example, for a 3.3V SiT1602 device with default drive strength setting, the typical rise/fall time is 1 ns for 15 pF output load. The typical rise/fall time slows down to 2.6 ns when the output load increases to 45 pF. One can choose to speed up the rise/fall time to 1.83 ns by then increasing the drive strength setting on the SiT1602.

The SiT1602 can support up to 60 pF or higher in maximum capacitive loads with drive strength settings. Refer to the Rise/Tall Time Tables (Table 7 to 11) to determine the proper drive strength for the desired combination of output load vs. rise/fall time.

#### SiT1602 Drive Strength Selection

Tables 7 through 11 define the rise/fall time for a given capacitive load and supply voltage.

- 1. Select the table that matches the SiT1602 nominal supply voltage (1.8V, 2.5V, 2.8V, 3.0V, 3.3V).
- 2. Select the capacitive load column that matches the application requirement (5 pF to 60 pF)
- 3. Under the capacitive load column, select the desired rise/fall times.
- 4. The left-most column represents the part number code for the corresponding drive strength.
- 5. Add the drive strength code to the part number for ordering purposes.

#### **Maximum Frequency Calculation**

Any given rise/fall time in Table 7 through 11 dictates the maximum frequency under which the oscillator can operate with guaranteed full output swing over the entire operating temperature range. This max frequency can be calculated as the following:

$$Max Frequency = \frac{1}{5 \times Trf_{20/80}}$$

where Trf\_20/80 is the typical value for 20%-80% rise/fall time.

#### Example 1

Calculate f<sub>MAX</sub> for the following condition:

- Vdd = 1.8V (Table 1)
- · Capacitive Load: 30 pF
- Desired Tr/f time = 3 ns (rise/fall time part number code = E)
- $f_{MAX} = 66.66660$

Part number for the above example:

SiT1602BIE12-18E-66.66660



Drive strength code is inserted here. Default setting is "-"

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Rise/Fall Time (20% to 80%) vs  $C_{LOAD}$  Tables

Table 7. Vdd = 1.8V Rise/Fall Times for Specific  $C_{LOAD}$ 

Rise/Fall Time Typ (ns)							
Drive Strength \ $C_{LOAD}$	5 pF	15 pF	30 pF	45 pF	60 pF		
L	6.16	11.61	22.00	31.27	39.91		
Α	3.19	6.35	11.00	16.01	21.52		
R	2.11	4.31	7.65	10.77	14.47		
В	1.65	3.23	5.79	8.18	11.08		
T	0.93	1.91	3.32	4.66	6.48		
E	0.78	1.66	2.94	4.09	5.74		
U	0.70	1.48	2.64	3.68	5.09		
F or "-": default	0.65	1.30	2.40	3.35	4.56		

Table 9. Vdd = 2.8V Rise/Fall Times for Specific C<sub>LOAD</sub>

Rise/Fall Time Typ (ns)								
Drive Strength \ C <sub>LOAD</sub> 5 pF 15 pF 30 pF 45 pF 60 pF								
L	3.77	7.54	12.28	19.57	25.27			
Α	1.94	3.90	7.03	10.24	13.34			
R	1.29	2.57	4.72	7.01	9.06			
В	0.97	2.00	3.54	5.43	6.93			
T	0.55	1.12	2.08	3.22	4.08			
E or "-": default	0.44	1.00	1.83	2.82	3.67			
U	0.34	0.88	1.64	2.52	3.30			
F	0.29	0.81	1.48	2.29	2.99			

Table 11. Vdd = 3.3V Rise/Fall Times for Specific C<sub>LOAD</sub>

	Rise/Fa							
Drive Strength $\ \ C_{LOAD}$	5 pF   15 pF   30 pF   45 pF   60							
L	3.39	6.88	11.63	17.56	23.59			
Α	1.74	3.50	6.38	8.98	12.19			
R	1.16	2.33	4.29	6.04	8.34			
В	0.81	1.82	3.22	4.52	6.33			
T or "-": default	0.46	1.00	1.86	2.60	3.84			
E	0.33	0.87	1.64	2.30	3.35			
U	0.28	0.79	1.46	2.05	2.93			
F	0.25	0.72	1.31	1.83	2.61			

Table 8. Vdd = 2.5V Rise/Fall Times for Specific C<sub>LOAD</sub>

Rise/Fall Time Typ (ns)									
Drive Strength \ C <sub>LOAD</sub>	Drive Strength \ C <sub>LOAD</sub> 5 pF 15 pF 30 pF 45 pF 60 pF								
L	4.13	8.25	12.82	21.45	27.79				
Α	2.11	4.27	7.64	11.20	14.49				
R	1.45	2.81	5.16	7.65	9.88				
В	1.09	2.20	3.88	5.86	7.57				
T	0.62	1.28	2.27	3.51	4.45				
E or "-": default	0.54	1.00	2.01	3.10	4.01				
U	0.43	0.96	1.81	2.79	3.65				
F	0.34	0.88	1.64	2.54	3.32				

Table 10. Vdd = 3.0V Rise/Fall Times for Specific  $C_{LOAD}$ 

Rise/Fall Time Typ (ns)									
Drive Strength \ C <sub>LOAD</sub>	ve Strength \ C <sub>LOAD</sub> 5 pF 15 pF 30 pF 45 pF 60 pF								
L	3.60	7.21	11.97	18.74	24.30				
Α	1.84	3.71	6.72	9.86	12.68				
R	1.22	2.46	4.54	6.76	8.62				
В	0.89	1.92	3.39	5.20	6.64				
T or "-": default	0.51	1.00	1.97	3.07	3.90				
E	0.38	0.92	1.72	2.71	3.51				
U	0.30	0.83	1.55	2.40	3.13				
F	0.27	0.76	1.39	2.16	2.85				

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## Pin 1 Configuration Options (OE, ST, or NC)

Pin 1 of the SiT1602 can be factory-programmed to support three modes: Output Enable (OE), standby  $(\overline{ST})$  or No Connect (NC). These modes can also be programmed with the Time Machine using field programmable devices.

#### Output Enable (OE) Mode

In the OE mode, applying logic Low to the OE pin only disables the output driver and puts it in Hi-Z mode. The core of the device continues to operate normally. Power consumption is reduced due to the inactivity of the output. When the OE pin is pulled High, the output is typically enabled in <1  $\mu$ s.

## Standby (ST) Mode

In the  $\overline{ST}$  mode, a device enters into the standby mode when Pin 1 pulled Low. All internal circuits of the device are turned off. The current is reduced to a standby current, typically in the range of a few  $\mu A$ . When  $\overline{ST}$  is pulled High, the device goes through the "resume" process, which can take up to 5 ms.

#### No Connect (NC) Mode

In the NC mode, the device always operates in its normal mode and outputs the specified frequency regardless of the logic level on pin 1.

Table 12 below summarizes the key relevant parameters in the operation of the device in OE. ST. or NC mode.

Table 12. OE vs. ST vs. NC

	OE	ST	NC
Active current 20 MHz (max, 1.8V)	4.1 mA	4.1 mA	4.1 mA
OE disable current (max. 1.8V)	4 mA	N/A	N/A
Standby current (typical 1.8V)	N/A	0.6 μΑ	N/A
OE enable time at 77.76 MHz (max)	138 ns	N/A	N/A
Resume time from standby (max, all frequency)	N/A	5 ms	N/A
Output driver in OE disable/standby mode	High Z	weak pull-down	N/A

#### **Output on Startup and Resume**

The SiT1602 comes with gated output. Its clock output is accurate to the rated frequency stability within the first pulse from initial device startup or resume from the standby mode.

In addition, the SiT1602 features "no runt" pulses and "no glitch" output during startup or resume as shown in the waveform captures in Figure 17 and Figure 18.



Figure 17. Startup Waveform vs. Vdd

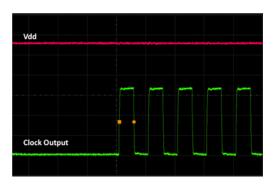


Figure 18. Startup Waveform vs. Vdd (Zoomed-in View of Figure 17)

# Instant Samples with Time Machine and Field Programmable Oscillators

SiTime supports a field programmable version of the SiT1602 low power oscillator for fast prototyping and real time customization of features. The <u>field programmable devices</u> (FP devices) are available for all five standard SiT1602 package sizes and can be configured to one's exact specification using the <u>Time Machine II</u>, an USB powered MEMS oscillator programmer.

#### Customizable Features of the SiT1602 FP Devices Include

- 52 standard frequencies between 3.75 MHz and 77.76 MHz (Refer to the frequency list on page 12)
- Three frequency stability options, ±20 ppm, ±25 ppm, ±50 ppm
- Two operating temperatures, -20 to 70°C or -40 to 85°C
- Six supply voltage options, 1.8V, 2.5V, 2.8V, 3.0V, 3.3V and 2.25 to 3.65V continuous
- · Output drive strength
- · OE, ST or NC mode

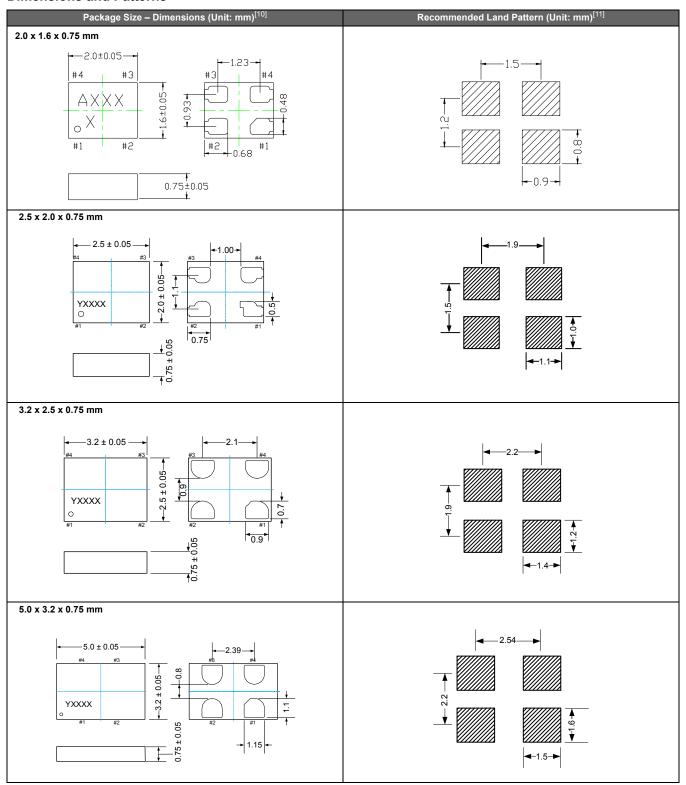
For more information regarding SiTime's field programmable solutions, visit <a href="http://www.sitime.com/time-machine">http://www.sitime.com/time-machine</a> and <a href="http://www.sitime.com/fo-devices">http://www.sitime.com/fo-devices</a>.

SiT1602 is typically factory-programmed per customer ordering codes for volume delivery.

# Low Power, Standard Frequency Oscillator



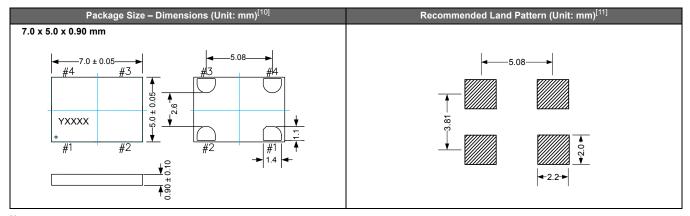
#### **Dimensions and Patterns**



# Low Power, Standard Frequency Oscillator



#### **Dimensions and Patterns**



#### Notes:

- 10. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
- 11. A capacitor of value 0.1  $\mu F$  or higher between Vdd and GND is required.

# Low Power, Standard Frequency Oscillator



### **Ordering Information**

The Part No. Guide is for reference only. To customize and build an exact part number, use the SiTime <u>Part Number</u> <u>Generator</u>.

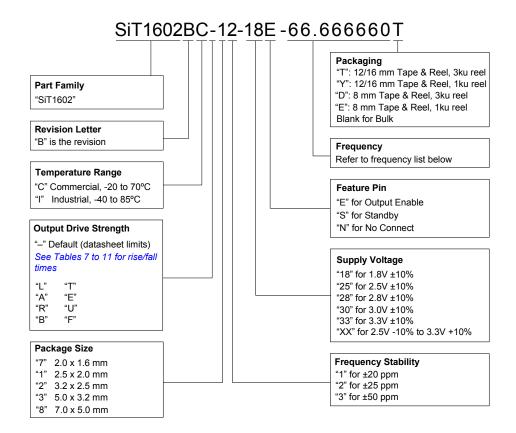


Table 13. List of Supported Frequencies

3.57 MHz	4 MHz	4.096 MHz	6 MHz	7.3728 MHz	8.192 MHz	10 MHz	12 MHz	14 MHz
18.432 MHz	19.2 MHz	20 MHz	24 MHz	24.576 MHz	25 MHz	25.000625 MHz	26 MHz	27 MHz
28.6363 MHz	30 MHz	31.25 MHz	32.768 MHz	33 MHz	33.3 MHz	33.33 MHz	33.333 MHz	33.3333 MHz
33.33333 MHz	35.84 MHz	37.5 MHz	38 MHz	38.4 MHz	40 MHz	40.5 MHz	48 MHz	50 MHz
54 MHz	60 MHz	62.5 MHz	65 MHz	66 MHz	66.6 MHz	66.66 MHz	66.666 MHz	66.6666 MHz
66.66666 MHz	72 MHz	74.175824 MHz	74.176 MHz	74.25 MHz	75 MHz	77.76 MHz		

Table 14. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	16 mm T&R (3ku)	16 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	8 mm T&R (3ku)	8 mm T&R (1ku)
2.0 x 1.6	_	-	_	-	D	E
2.5 x 2.0	_	-	_	-	D	E
3.2 x 2.5	_	-	_	-	D	E
5.0 x 3.2	-	-	Т	Y	-	-
7.0 x 5.0	Т	Y	-	-	-	-

# Low Power, Standard Frequency Oscillator



#### Table 15. Additional Information

Document	Description	Download Link
Time Machine II	MEMS oscillator programmer	http://www.sitime.com/support/time-machine-oscillator-programmer
Field Programmable Oscillators	Devices that can be programmable in the field by Time Machine II	http://www.sitime.com/products/field-programmable-oscillators
Manufacturing Notes	Tape & Reel dimension, reflow profile and other manufacturing related info	http://www.sitime.com/component/docman/doc_download/243-manufacturing-notes-for-sitime-oscillators
Qualification Reports	RoHS report, reliability reports, composition reports	http://www.sitime.com/support/quality-and-reliability
Performance Reports	Additional performance data such as phase noise, current consumption and jitter for selected frequencies	http://www.sitime.com/support/performance-measurement-report
Termination Techniques	Termination design recommendations	http://www.sitime.com/support/application-notes
Layout Techniques	Layout recommendations	http://www.sitime.com/support/application-notes

#### **Revision History**

#### Table 16. Datasheet Version and Change Log

Version	Release Date	Change Summary
0.9	4/1/14	Preliminary
1.0	5/14/14	Removed preliminary Updated max spec for current consumption and OE disable current Updated the maximum operating junction temperature Updated the current consumption and OE disable current in Table 12 Updated performance plots 8 and 10 Revised the formula for calculating the max frequency with different rise/fall time options
1.01	5/07/15	Added 20 MHz to the frequency selection     Revised the Electrical Characteristics, Timing Diagrams and Performance Plots     Revised 2016 PKG diagram
1.02	6/18/15	Added 16 mm T&R information to Table 14     Revised 12 mm T&R information to Table 14

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# **Supplemental Information**

The Supplemental Information section is not part of the datasheet and is for informational purposes only.



# Silicon MEMS Outperforms Quartz

# Silicon MEMS Outperforms Quartz



#### **Best Reliability**

Silicon is inherently more reliable than quartz. Unlike quartz suppliers, SiTime has in-house MEMS and analog CMOS expertise, which allows SiTime to develop the most reliable products. Figure 1 shows a comparison with quartz technology.

#### Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal™ process, which eliminates foreign particles and improves long term aging and reliability
- · World-class MEMS and CMOS design expertise

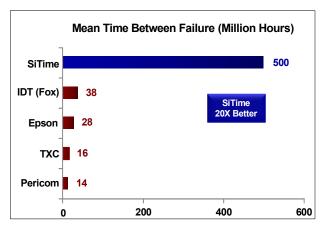


Figure 1. Reliability Comparison<sup>[1]</sup>

#### **Best Aging**

Unlike quartz, MEMS oscillators have excellent long term aging performance which is why every new SiTime product specifies 10-year aging. A comparison is shown in Figure 2.

#### Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal process, which eliminates foreign particles and improves long term aging and reliability
- Inherently better immunity of electrostatically driven MEMS resonator

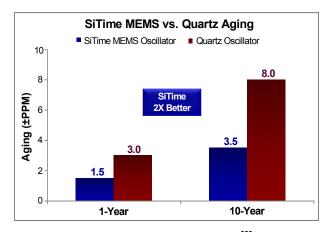


Figure 2. Aging Comparison<sup>[2]</sup>

#### **Best Electro Magnetic Susceptibility (EMS)**

SiTime's oscillators in plastic packages are up to 54 times more immune to external electromagnetic fields than quartz oscillators as shown in Figure 3.

#### Why is SiTime Best in Class:

- Internal differential architecture for best common mode noise rejection
- Electrostatically driven MEMS resonator is more immune to EMS

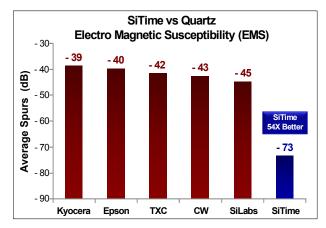


Figure 3. Electro Magnetic Susceptibility (EMS)[3]

#### **Best Power Supply Noise Rejection**

SiTime's MEMS oscillators are more resilient against noise on the power supply. A comparison is shown in Figure 4.

#### Why is SiTime Best in Class:

- On-chip regulators and internal differential architecture for common mode noise rejection
- · Best analog CMOS design expertise

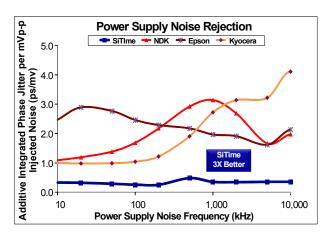


Figure 4. Power Supply Noise Rejection<sup>[4]</sup>

# Silicon MEMS Outperforms Quartz



#### **Best Vibration Robustness**

High-vibration environments are all around us. All electronics, from handheld devices to enterprise servers and storage systems are subject to vibration. Figure 5 shows a comparison of vibration robustness.

#### Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than guartz
- Center-anchored MEMS resonator is the most robust design

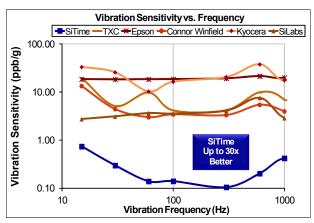


Figure 5. Vibration Robustness<sup>[5]</sup>

#### Notes:

- 1. Data Source: Reliability documents of named companies.
- 2. Data source: SiTime and quartz oscillator devices datasheets.
- 3. Test conditions for Electro Magnetic Susceptibility (EMS):
  - According to IEC EN61000-4.3 (Electromagnetic compatibility standard)
  - Field strength: 3V/m
  - Radiated signal modulation: AM 1 kHz at 80% depth
  - Carrier frequency scan: 80 MHz 1 GHz in 1% steps
  - · Antenna polarization: Vertical
  - DUT position: Center aligned to antenna

#### Devices used in this test:

SiTime, SiT9120AC-1D2-33E156.250000 - MEMS based - 156.25 MHz

Epson, EG-2102CA 156.2500M-PHPAL3 - SAW based - 156.25 MHz

TXC, BB-156.250MBE-T - 3rd Overtone quartz based - 156.25 MHz

Kyocera, KC7050T156.250P30E00 - SAW based - 156.25 MHz

Connor Winfield (CW), P123-156.25M - 3rd overtone quartz based - 156.25 MHz

SiLabs, Si590AB-BDG - 3rd overtone quartz based - 156.25 MHz

4. 50 mV pk-pk Sinusoidal voltage.

#### Devices used in this test:

SiTime, SiT8208AI-33-33E-25.000000, MEMS based - 25 MHz

NDK, NZ2523SB-25.6M - quartz based - 25.6 MHz

Kyocera, KC2016B25M0C1GE00 - quartz based - 25 MHz

Epson, SG-310SCF-25M0-MB3 - quartz based - 25 MHz

- 5. Devices used in this test: same as EMS test stated in Note 3.
- 6. Test conditions for shock test:
  - MIL-STD-883F Method 2002
  - Condition A: half sine wave shock pulse, 500-g, 1ms
  - $\bullet$  Continuous frequency measurement in 100  $\mu s$  gate time for 10 seconds

Devices used in this test: same as EMS test stated in Note 3

7. Additional data, including setup and detailed results, is available upon request to qualified customers. Please contact productsupport@sitime.com.

#### **Best Shock Robustness**

SiTime's oscillators can withstand at least  $50,000\ g$  shock. They all maintain their electrical performance in operation during shock events. A comparison with quartz devices is shown in Figure 6.

#### Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than guartz
- Center-anchored MEMS resonator is the most robust design

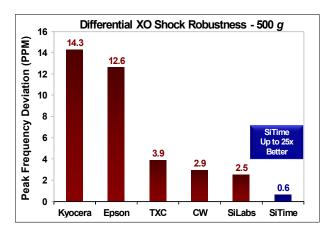


Figure 6. Shock Robustness<sup>[6]</sup>

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